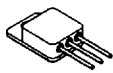
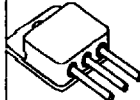


NEW ENGLAND SEMICONDUCTOR

INSULATED GATE BIPOLAR TRANSISTOR

PACKAGE	DEVICE TYPE	BV_{CES} VOLTS	I_C (CONT) AMPS	$V_{CE(sat)}$ VOLTS	t_f (1) nsec *	C_{IES} * pf	$\theta_{j/c}$ * $^{\circ}C/W$
TO-257 	NSG30620	600	20	2.6	570	750	2.0
	NSG30620A	600	20	3.1	310	750	2.0
TO-254 	NSG20640	600@ 90 $^{\circ}C$	31	2.0	800	1500	1.25
	NSG20648A	600@ 90 $^{\circ}C$	24	2.9	100	1500	1.25
	NSG21034	1000	34	3.6	750	1500	1.25
TO-258 	NSG40635	600	35	2.7	250	1200	1.10
	NSG40640	600	40	2.0	800	1500	1.0
	NSG40648A	600	48	2.9	100	1500	1.0
	NSG40660A	600	60	3.1	125	2500	0.85
	NSG40675	600	75	2.0	400	4000	0.75
	NSG40675A	600	75	2.9	175	4000	0.75
	NSG41045	1000	45	3.2	300	2100	0.75
	NSG41065	1000	65	3.2	300	3500	0.75
	NSG41270A	1200	70	4.2	500	4300	0.75
	NSG41275A	1200	75	3.2	1200	4300	0.75

• Electrical Characteristics @ 25 $^{\circ}C$ unless otherwise noted

(1) t_f is a function of R_G

* Typical